



## TO-126 Plastic-Encapsulate Transistors

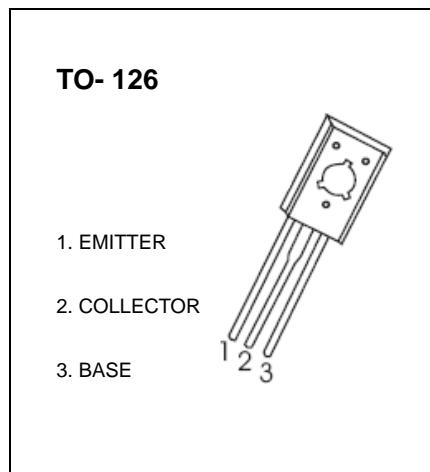
### 2SB649/2SB649A TRANSISTOR (PNP)

#### FEATURES

Low Frequency Power Amplifier Complementary Pair  
with 2SD669/A

#### MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-180	V
$V_{CEO}$	Collector-Emitter Voltage 2SB649	-120	V
	2SB649A	-160	
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current –Continuous	-1.5	A
$P_c$	Collector Power Dissipation	1	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$



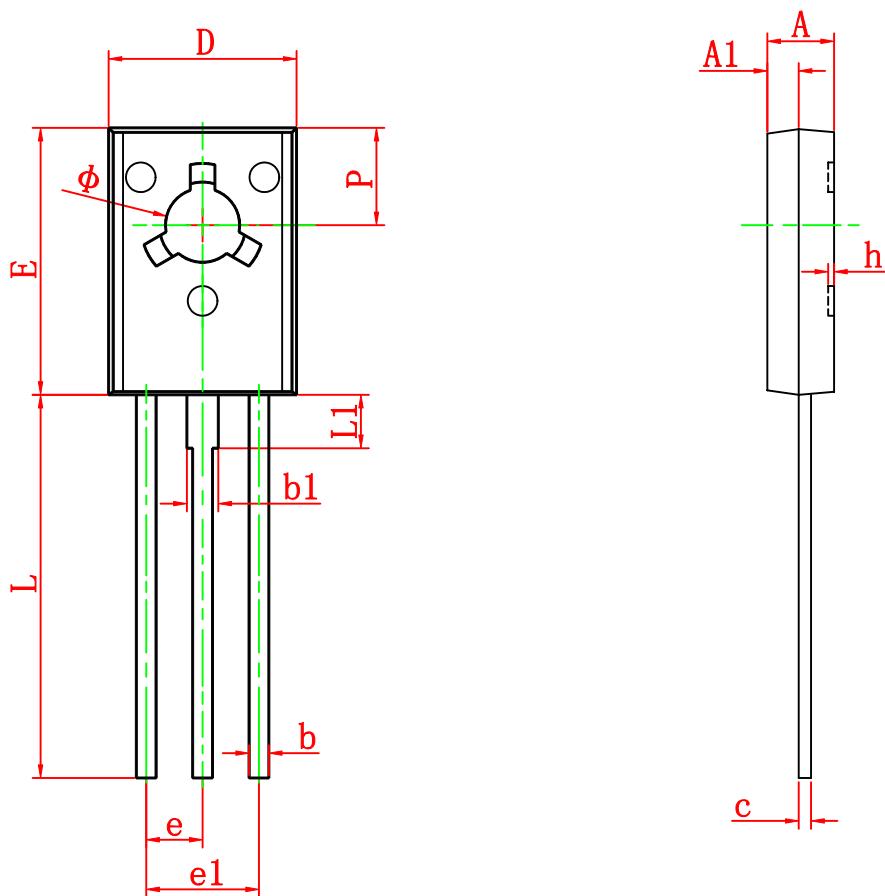
#### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -1\text{mA}, I_E = 0$	-180			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	2SB649	-120		V
			2SB649A	-160		
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1\text{mA}, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -160\text{V}, I_E = 0$			-10	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4\text{V}, I_C = 0$			-10	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE} = -5\text{V}, I_C = -150\text{mA}$ 2SB649	60		320	
	$h_{FE(2)}$	$V_{CE} = -5\text{V}, I_C = -500\text{mA}$	60		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$			-1	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = -5\text{V}, I_C = -150\text{mA}$			-1.5	V
Transition frequency	$f_T$	$V_{CE} = -5\text{V}, I_C = -150\text{mA}$		140		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		27		pF

#### CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C	D
Range 2SB649	60-120	100-200	160-320
2SB649A	60-120	100-200	

## TO-126 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.500	2.900	0.098	0.114
A1	1.100	1.500	0.043	0.059
b	0.660	0.860	0.026	0.034
b1	1.170	1.370	0.046	0.054
c	0.450	0.600	0.018	0.024
D	7.400	7.800	0.291	0.307
E	10.600	11.000	0.417	0.433
e	2.290 TYP		0.090 TYP	
e1	4.480	4.680	0.176	0.184
h	0.000	0.300	0.000	0.012
L	15.300	15.700	0.602	0.618
L1	2.100	2.300	0.083	0.091
P	3.900	4.100	0.154	0.161
Φ	3.000	3.200	0.118	0.126

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